NSN 5961-01-044-5845

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

1.253 inches

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-4

Electrode Internally-electrically Connected To Case:

Cathode

Mounting Method:

Threaded stud

Overall Width Across Flats:

Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 reverse voltage, instantaneous and 50.0 working peak reverse voltage

Current Rating Per Characteristic:

400.00 amperes forward current, average preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 1 tab, solder lug

Specification Data:

81349-mil-prf-19500/478 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.